

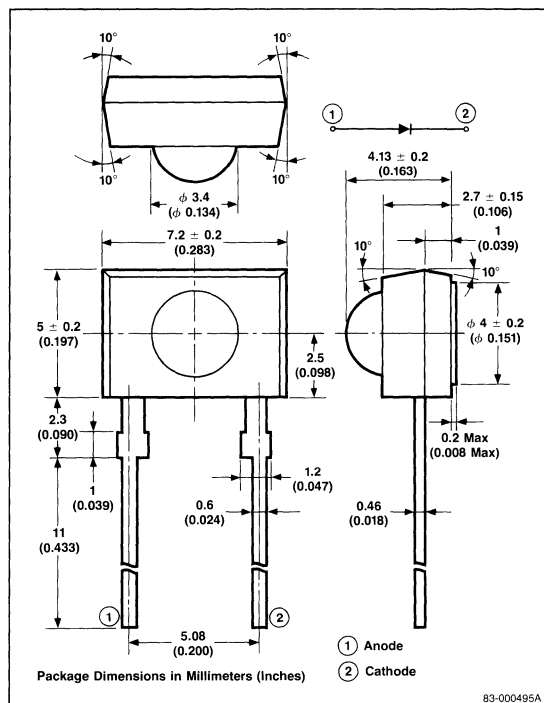
Description

The PH309 is a photo diode with a PIN structure. It has a wide photo-receiving area and high-speed response enabling applications for various types of remote control equipment. The resin material used for the package has the filter effect of transmitting infrared radiation.

Features

- Ultrahigh-speed response (t_r , t_f = 30ns)
- The wavelength of maximum sensitivity matches that of an infrared LED (λ_{S-MAX} = 940nm)
- High sensitivity (31nA/lx)
- Wide dynamic range

Package Dimensions



Absolute Maximum Ratings

$T_A = +25^\circ\text{C}$

Reverse Voltage, V_R	20V
Power Dissipation, P_D	150mW
Junction Temperature, T_J	80°C
Storage Temperature, T_{STG}	-40°C to +80°C

Electro-Optical Characteristics

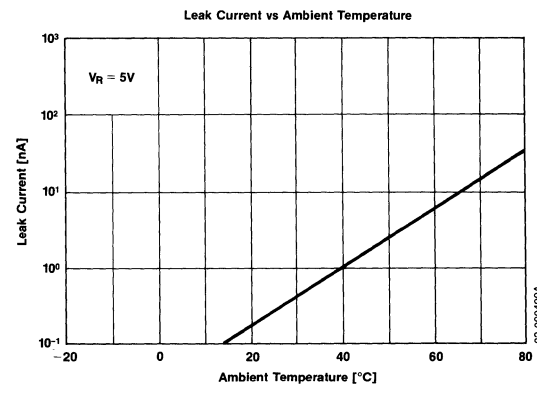
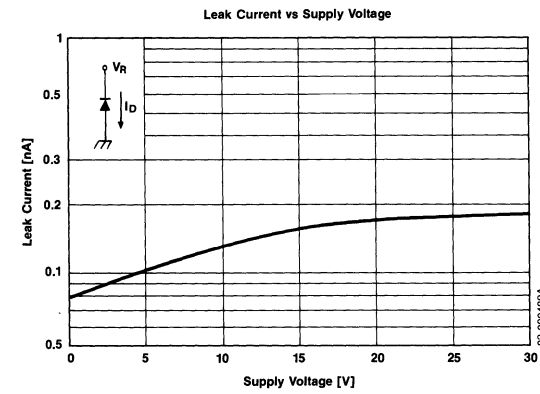
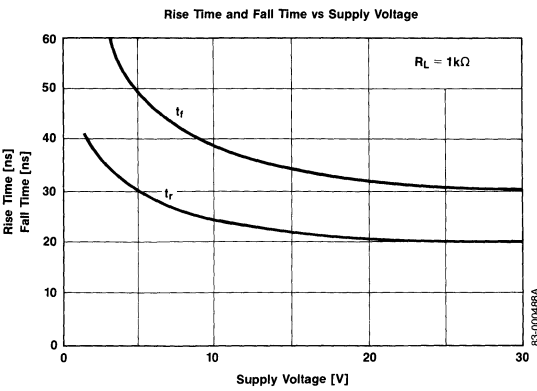
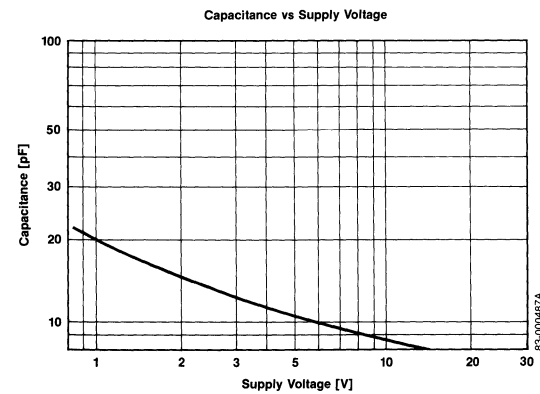
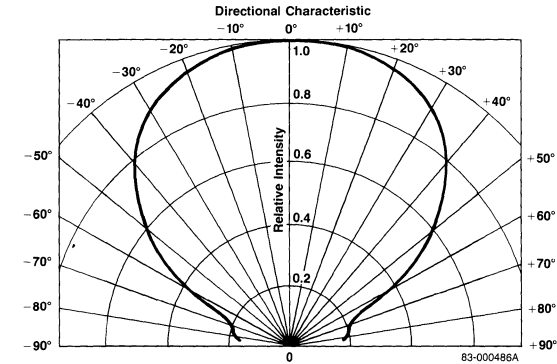
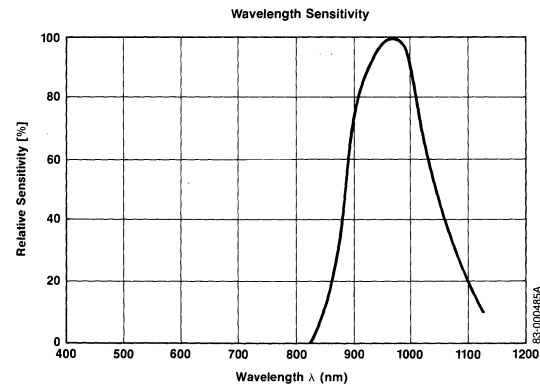
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Parameters	Symbol	Limits			Test Conditions
		Min	Typ	Max	
Dark Current	I_R			30	nA $V_R = 10V$
Wavelength of Maximum Sensitivity	λ_{MAX}		940		nm
Quantum Yield	η		0.88		$\lambda = 940\text{nm}$
Spectral Sensitivity	S		50		nA/lx $V_R = 5V$
Spectral Sensitivity	S_{IR}		4.7		μA $V_R = 5V$, $H = 0.1\text{mW/cm}^2$
Rise and Fall Time of the Photo Current from 10% to 90% and 90% to 10% of the Final Value	t_r , t_f		120		ns $R_L = 1k\Omega$, $V_R = 0V$, $\lambda = 940\text{nm}$
	t_r , t_f		30		ns $R_L = 1k\Omega$, $V_R = 5V$, $\lambda = 940\text{nm}$
Capacitance	C_T		11		pF $V_R = 5V$, $f = 1\text{MHz}$
Radiant Sensitive Area	A		5.3		mm ²

* $\lambda = 940\text{nm}$

Typical Characteristics

T_A = +25°C



Typical Characteristics (cont)

$T_A = +25^\circ\text{C}$

